	No.2487A	<h1 style="margin: 0;">2SC3466</h1> <p style="margin: 0;">NPN Triple Diffused Planar Type Silicon Transistor</p> <p style="margin: 0;">Switching Regulator Applications</p>
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Features

- . High breakdown voltage and high reliability
- . Fast switching speed
- . Wide ASO

Absolute Maximum Ratings at Ta=25°C

Collector-to-Base Voltage	V_{CB0}	1200	V
Collector-to-Emitter Voltage	V_{CEO}	650	V
Emitter-to-Base Voltage	V_{EBO}	7	V
Collector Current	I_C	8	A
Peak Collector Current	i_{cp}	20	A
Base Current	I_B	3	A
Collector Dissipation	P_C	120	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

$PW \leq 300\mu s, \text{duty cycle} \leq 10\%$

$T_c = 25^\circ C$

Electrical Characteristics at Ta=25°C

			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=650V, I_E=0$			100	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=5V, I_C=0$			100	μA
DC Current Gain	h_{FE1}	$V_{CE}=5V, I_C=1A$	10*		40*	
	h_{FE2}	$V_{CE}=5V, I_C=4A$	6			
Gain-Bandwidth Product	f_T	$V_{CE}=10V, I_C=1A$		5		MHz
Output Capacitance	c_{ob}	$V_{CB}=10V, f=1MHz$		120		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.8A$			3.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=4A, I_B=0.8A$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	1200			V

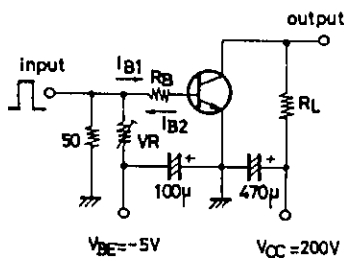
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*: The 2SC3466 is classified by 1A h_{FE} as follows:

10 K 20	15 L 30	20 M 40
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Switching Time Test Circuit

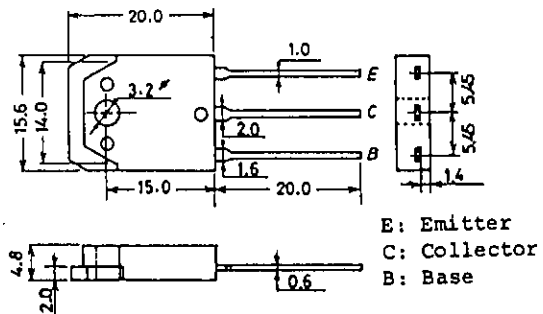
$PW=20\mu s, \text{duty factor} \leq 1\%$



Unit (Resistance : Ω, Capacitance : F)

Package Dimensions 2022

(unit:mm)

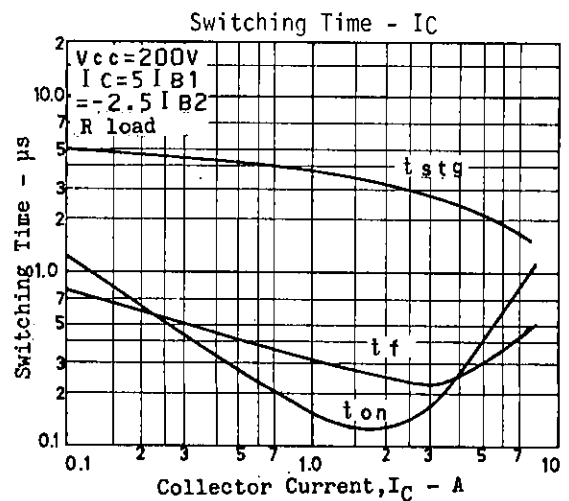
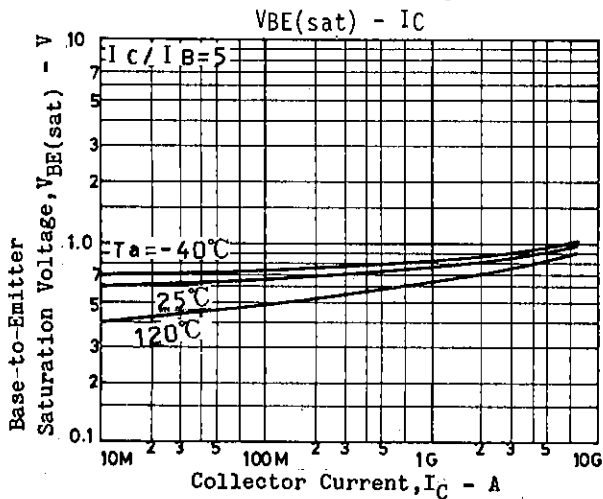
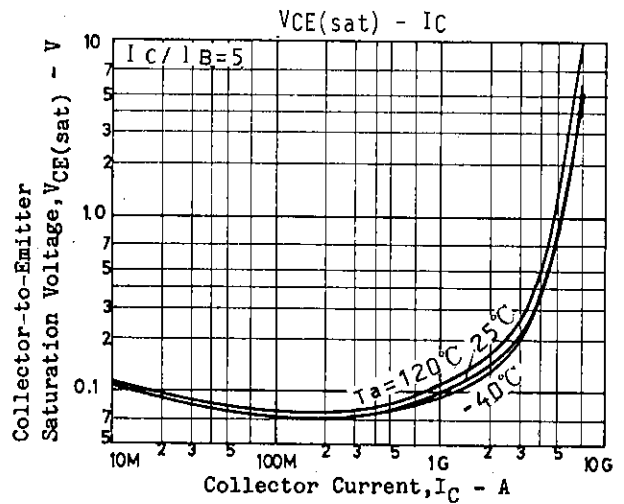
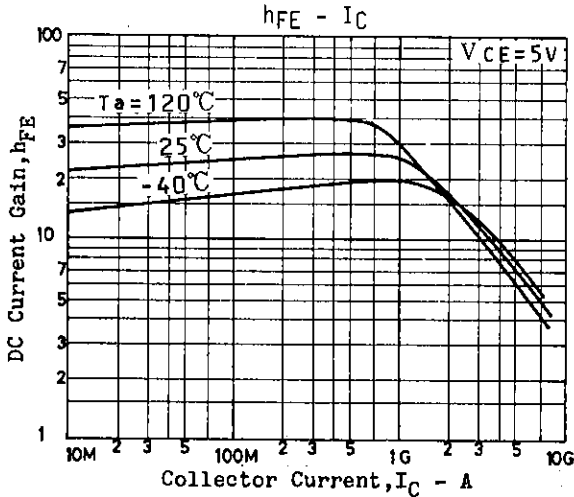
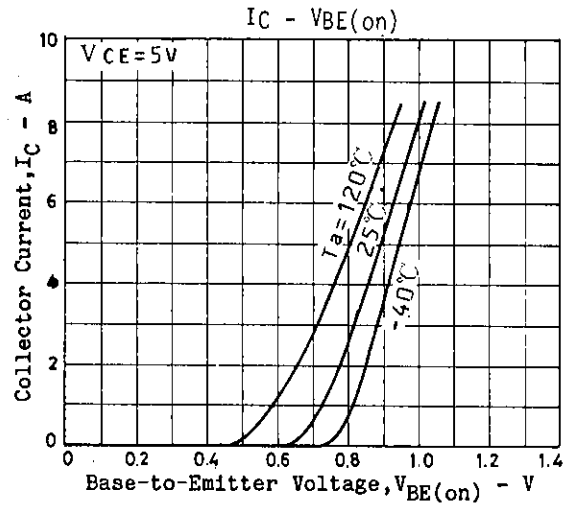
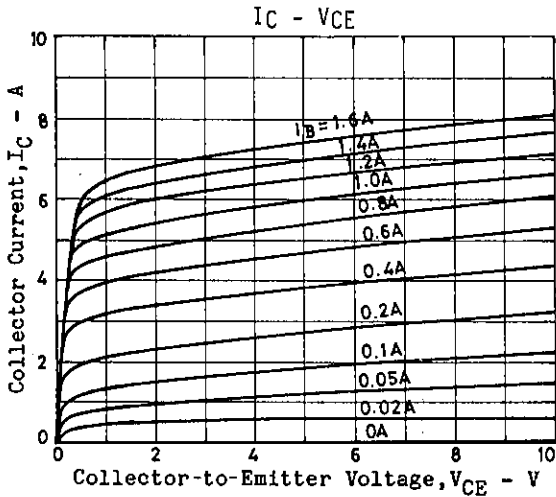


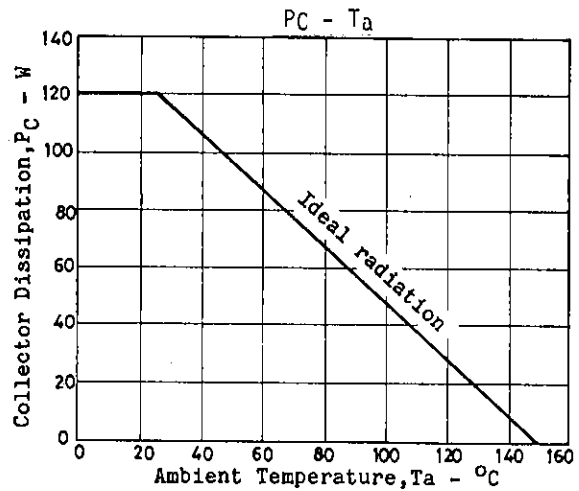
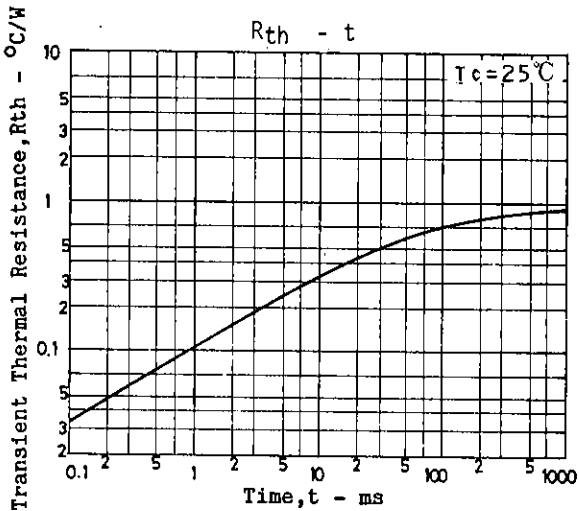
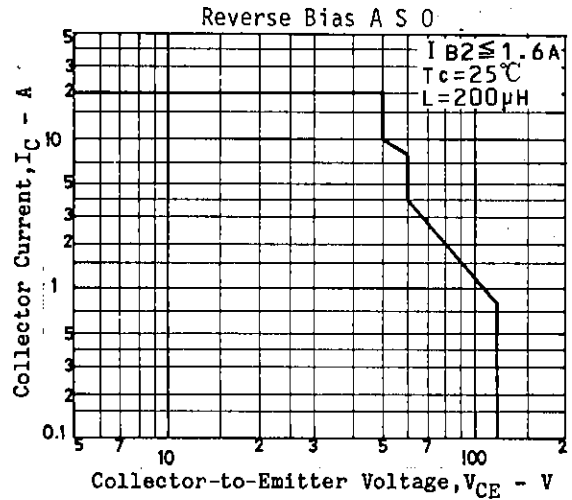
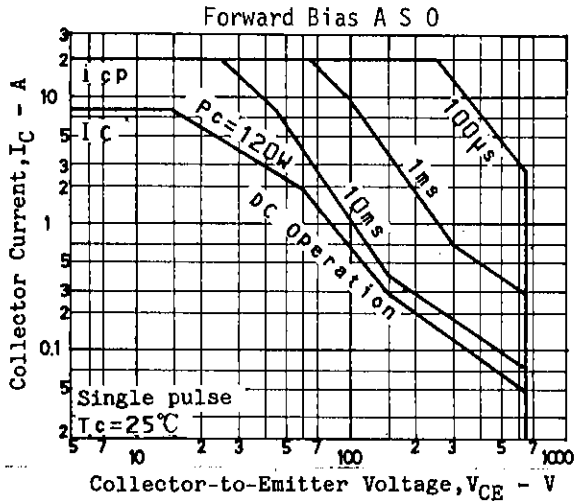
E: Emitter
C: Collector
B: Base

SANYO: TO3PB

Continued from preceding page.

			min	typ	max	unit
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	650			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
Turn-on Time	t_{on}	$V_{CC}=200V, 5I_{B1}=-2.5I_{B2}$ $=I_C=4A, R_L=50ohms$			1.0	μs
Storage Time	t_{stg}				4.0	μs
Fall Time	t_f				0.7	μs





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